

< Mono : 19.00% – 19.70% >

Dimension 156 mm x 156 mm ± 0.5 mm

Wafer Thickness 200µm ± 30µm  
180µm + 30µm / -20µm

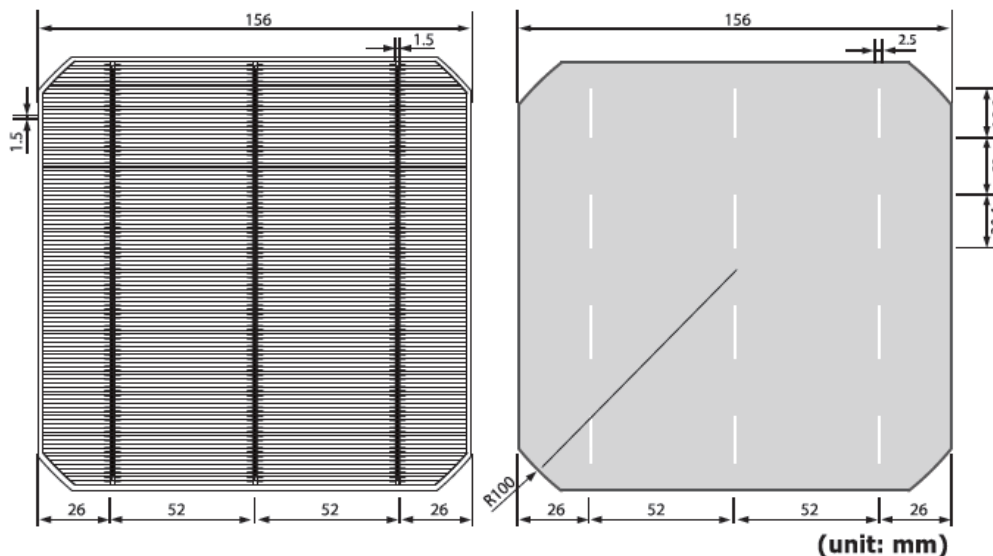
Front(-) Three 1.5mm wide bus bars (silver) with distance 52 mm,  
alkaline texturized surface with dark blue silicon nitride AR coating.

Back(+) 2.5mm wide silver/aluminum soldering pads, aluminum local back surface field.

Efficiency code	1900	1910	1920	1930	1940	1950	1960	1970
Efficiency (%)	19.0	19.1	19.2	19.3	19.4	19.5	19.6	19.7
Pmax (W)	4.540	4.564	4.588	4.612	4.636	4.660	4.683	4.707
Voc (V)	0.642	0.643	0.644	0.645	0.645	0.646	0.647	0.648
Isc (A)	8.931	8.958	8.985	9.007	9.029	9.055	9.080	9.105
Vmp (V)	0.541	0.543	0.545	0.546	0.547	0.549	0.550	0.552
Imp (A)	8.392	8.407	8.424	8.449	8.478	8.498	8.517	8.536

\*Data under standard testing conditions (STC): 1,000W/m<sup>2</sup>, AM1.5, 25°C, Pmax: Positive power tolerance.

Voltage -2.08 mV/K  
Current +4.51 mA/K  
Power -0.40 %/K



(unit: mm)

(Cell Efficiency 19.4 %)

